

**AOT8N60 / AOTF8N60**  
**600V, 8A N-Channel MOSFET**

formerly engineering part number AOT9606/AOTF9606

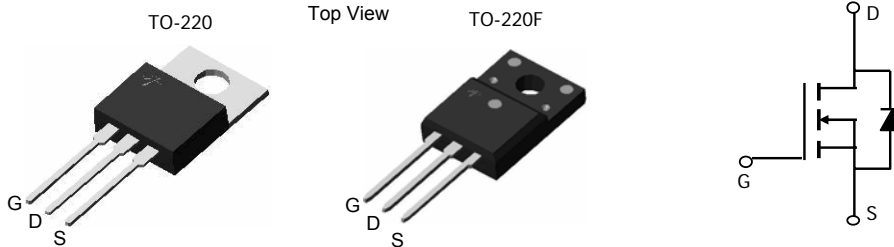

**General Description**

The AOT8N60 & AOTF8N60 have been fabricated using an advanced high voltage MOSFET process that is designed to deliver high levels of performance and robustness in popular AC-DC applications. By providing low  $R_{DS(on)}$ ,  $C_{iss}$  and  $C_{rss}$  along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

**Features**

$V_{DS}$  (V) = 700V @ 150°C  
 $I_D$  = 8A  
 $R_{DS(ON)}$  < 0.9  $\Omega$  ( $V_{GS}$  = 10V)

**100% UIS Tested!**  
**100%  $R_g$  Tested!**  
 **$C_{iss}$ ,  $C_{oss}$ ,  $C_{rss}$  Tested!**


**Absolute Maximum Ratings  $T_A=25^\circ\text{C}$  unless otherwise noted**

Parameter	Symbol	AOT8N60	AOTF8N60	Units
Drain-Source Voltage	$V_{DS}$	600		V
Gate-Source Voltage	$V_{GS}$	$\pm 30$		V
Continuous Drain Current <sup>B</sup>	$T_C=25^\circ\text{C}$	8	8*	A
	$T_C=100^\circ\text{C}$	5	5*	
Pulsed Drain Current <sup>C</sup>	$I_{DM}$	32		
Avalanche Current <sup>C</sup>	$I_{AR}$	3.2		A
Repetitive avalanche energy <sup>C</sup>	$E_{AR}$	150		mJ
Single pulsed avalanche energy <sup>G</sup>	$E_{AS}$	300		mJ
Peak diode recovery dv/dt	dv/dt	5		V/ns
Power Dissipation <sup>B</sup>	$T_C=25^\circ\text{C}$	147	50	W
	Derate above 25°C	1.17	0.4	W/°C
Junction and Storage Temperature Range	$T_J, T_{STG}$	-50 to 150		°C
Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds	$T_L$	300		°C

**Thermal Characteristics**

Parameter	Symbol	AOT8N60	AOTF8N60	Units
Maximum Junction-to-Ambient <sup>A</sup>	$R_{\theta JA}$	65	65	°C/W
Maximum Case-to-Sink <sup>A</sup>	$R_{\theta CS}$	0.5	-	°C/W
Maximum Junction-to-Case <sup>D,F</sup>	$R_{\theta JC}$	0.85	2.5	°C/W

\* Drain current limited by maximum junction temperature.

Electrical Characteristics ( $T_J=25^\circ\text{C}$  unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>STATIC PARAMETERS</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$I_D=250\mu\text{A}, V_{GS}=0\text{V}, T_J=25^\circ\text{C}$	600			V
		$I_D=250\mu\text{A}, V_{GS}=0\text{V}, T_J=150^\circ\text{C}$		700		V
$BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$		0.65		$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=600\text{V}, V_{GS}=0\text{V}$			1	$\mu\text{A}$
		$V_{DS}=480\text{V}, T_J=125^\circ\text{C}$			10	
$I_{GSS}$	Gate-Body leakage current	$V_{DS}=0\text{V}, V_{GS}=\pm 30\text{V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	3	3.8	5	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10\text{V}, I_D=4\text{A}$		0.74	0.9	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS}=40\text{V}, I_D=4\text{A}$		12.5		S
$V_{SD}$	Diode Forward Voltage	$I_S=1\text{A}, V_{GS}=0\text{V}$		0.73	1	V
$I_S$	Maximum Body-Diode Continuous Current				8	A
$I_{SM}$	Maximum Body-Diode Pulsed Current				32	A
<b>DYNAMIC PARAMETERS</b>						
$C_{iss}$	Input Capacitance	$V_{GS}=0\text{V}, V_{DS}=25\text{V}, f=1\text{MHz}$	912	1140	1370	pF
$C_{oss}$	Output Capacitance		87	109	131	pF
$C_{riss}$	Reverse Transfer Capacitance		6.2	7.8	9.5	pF
$R_g$	Gate resistance	$V_{GS}=0\text{V}, V_{DS}=0\text{V}, f=1\text{MHz}$	3.1	3.9	5.9	$\Omega$
<b>SWITCHING PARAMETERS</b>						
$Q_g$	Total Gate Charge	$V_{GS}=10\text{V}, V_{DS}=480\text{V}, I_D=8\text{A}$		28.4	35	nC
$Q_{gs}$	Gate Source Charge		5.8	7	nC	
$Q_{gd}$	Gate Drain Charge		13.4	17	nC	
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10\text{V}, V_{DS}=300\text{V}, I_D=8\text{A}, R_G=25\Omega$		30	40	ns
$t_r$	Turn-On Rise Time		63	75	ns	
$t_{D(off)}$	Turn-Off Delay Time		69	85	ns	
$t_f$	Turn-Off Fall Time		51	65	ns	
$t_{rr}$	Body Diode Reverse Recovery Time	$I_F=8\text{A}, di/dt=100\text{A}/\mu\text{s}, V_{DS}=100\text{V}$		270	324	ns
$Q_{rr}$	Body Diode Reverse Recovery Charge	$I_F=8\text{A}, di/dt=100\text{A}/\mu\text{s}, V_{DS}=100\text{V}$		3.3	4.0	$\mu\text{C}$

A: The value of  $R_{\theta JA}$  is measured with the device in a still air environment with  $T_A=25^\circ\text{C}$ .

B: The power dissipation  $P_D$  is based on  $T_{J(MAX)}=150^\circ\text{C}$ , using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature  $T_{J(MAX)}=150^\circ\text{C}$ .

D: The  $R_{\theta JA}$  is the sum of the thermal impedance from junction to case  $R_{\theta JC}$  and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using  $<300\mu\text{s}$  pulses, duty cycle 0.5% max.

F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of  $T_{J(MAX)}=150^\circ\text{C}$ .

G:  $L=60\text{mH}, I_{AS}=3.2\text{A}, V_{DD}=50\text{V}, R_G=25\Omega$ , Starting  $T_J=25^\circ\text{C}$

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

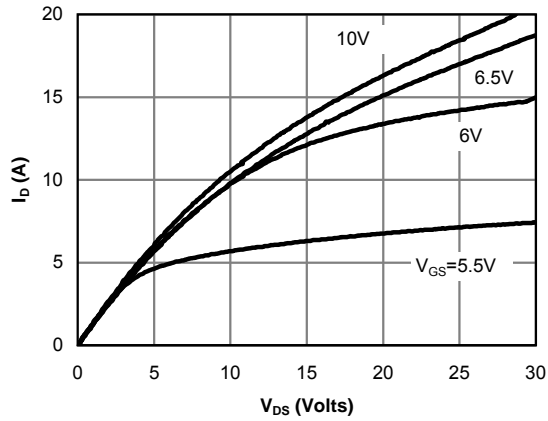


Fig 1: On-Region Characteristics

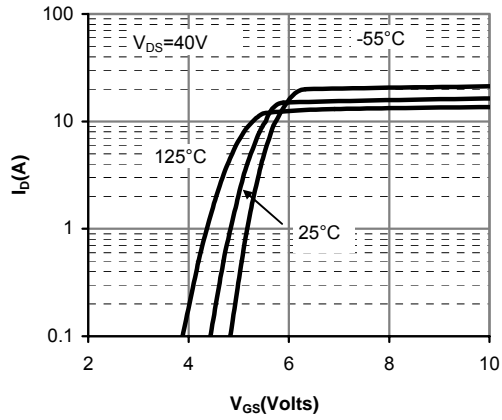


Figure 2: Transfer Characteristics

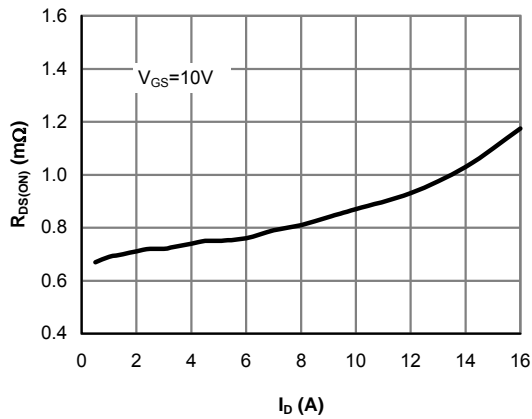


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

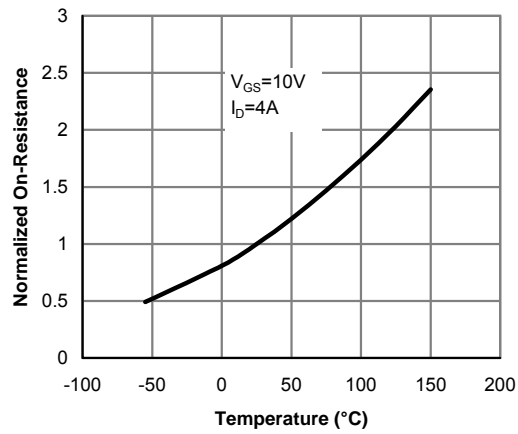


Figure 4: On-Resistance vs. Junction Temperature

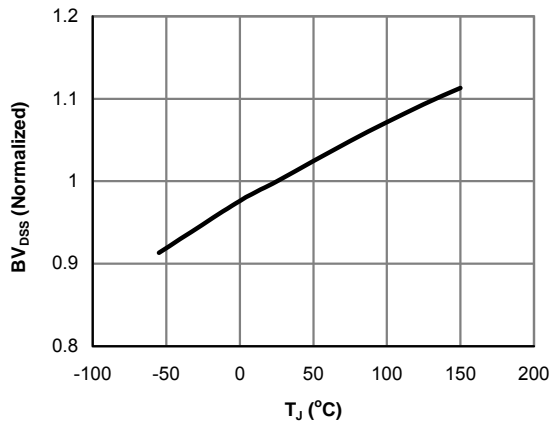


Figure 5: Break Down vs. Junction Temperature

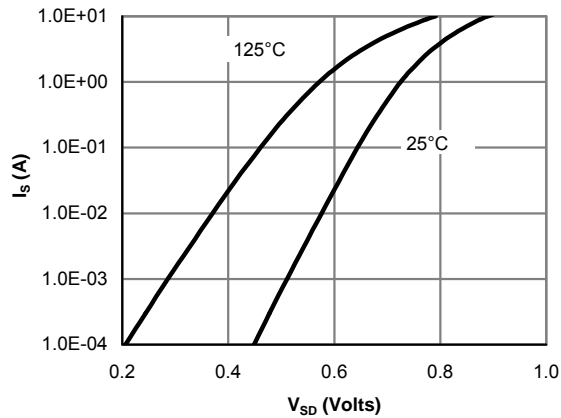


Figure 6: Body-Diode Characteristics

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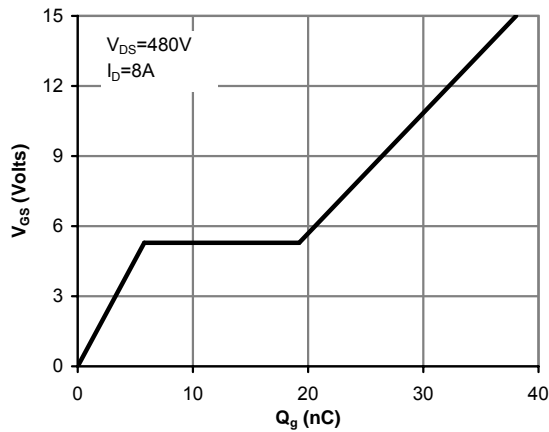


Figure 7: Gate-Charge Characteristics

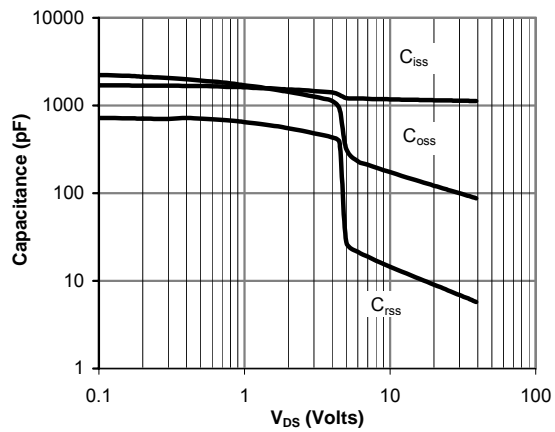


Figure 8: Capacitance Characteristics

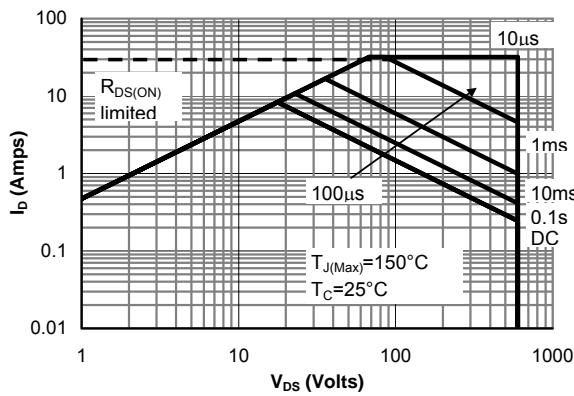


Figure 9: Maximum Forward Biased Safe Operating Area for AOT8N60 (Note F)

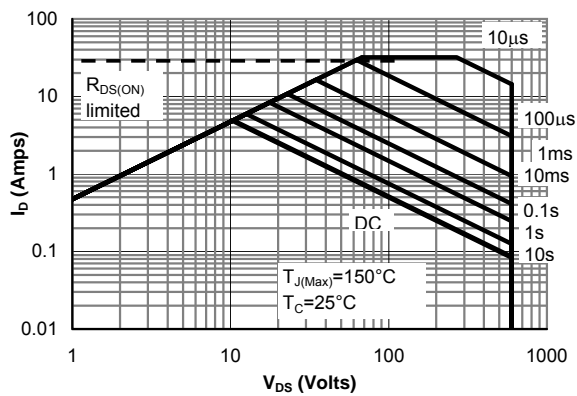


Figure 10: Maximum Forward Biased Safe Operating Area for AOTF8N60 (Note F)

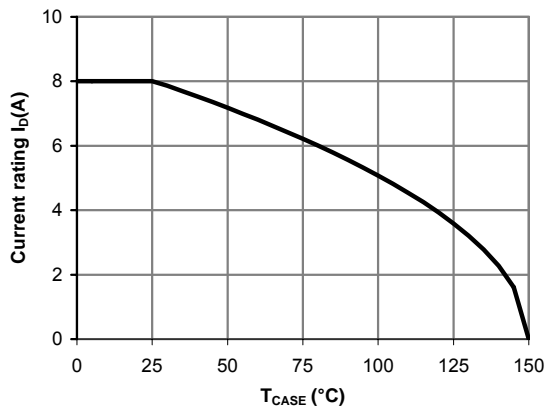


Figure 11: Current De-rating (Note B)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

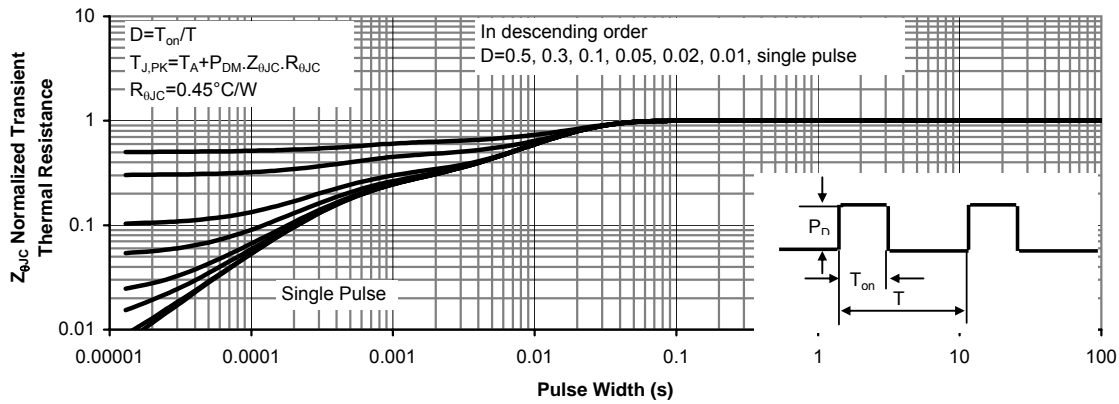


Figure 12: Normalized Maximum Transient Thermal Impedance for AOT8N60 (Note F)

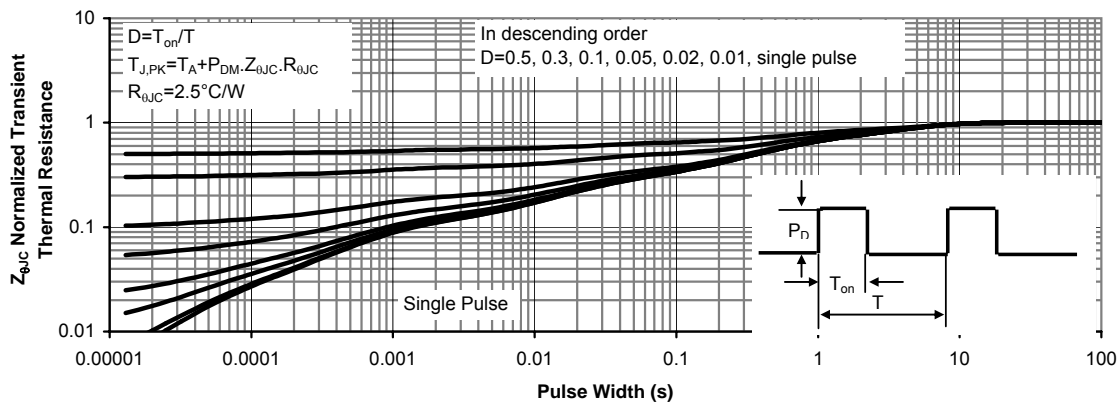
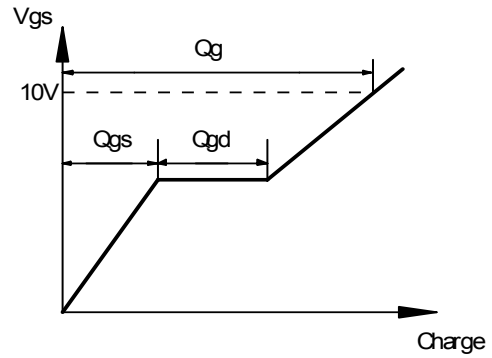
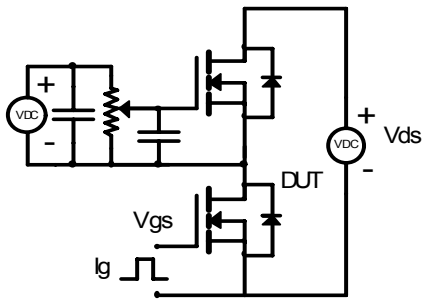
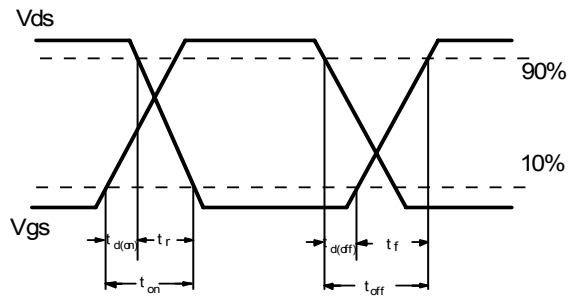
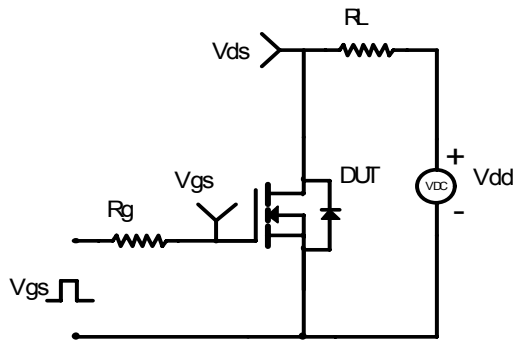


Figure 13: Normalized Maximum Transient Thermal Impedance for AOTF8N60 (Note F)

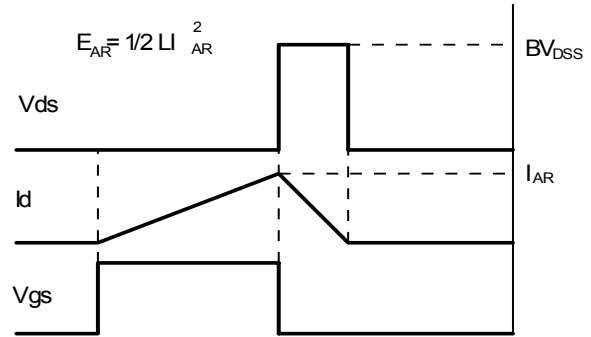
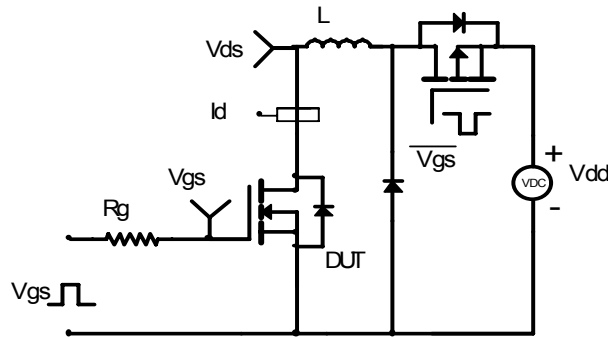
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

